

# 2200nm InGaAs 1000um PD Chip datasheet

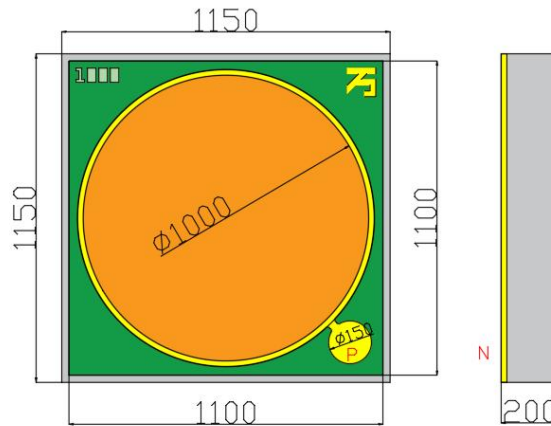
P/N : WIR4-1000

## Application

Optical sensor  
Gas sensor for CO<sub>2</sub>  
Optical power meter  
900-2200nm Spectral range

## Structure

InGaAs / InP PIN Chip.  
P Electrode (anode) : Gold.  
N Electrode (cathode) : Gold.



## DIMENSIONS

Conditions	Min.	Typ.	Max	Unit
Active	995	1000	1005	μm
Chip width	1130	1150	1170	μm
Chip length	1130	1150	1170	μm
Chip height	180	200	220	μm
Pad Area	140	150	160	μm

## Electro-Optical Characteristics ( @ Ta=25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Dark current	Id	Vr=-0.5V			9	uA
Responsivity	R	Vr=0V,@2000 nm	1.0	1.2	-	A/W
Capacitance	Cp	Vr=0V, f=1MHz		440	1000	pF
Wavelength range	λ		900	2004	2200	nm

## ABSOLUTE MAXIMUM RATING

Parameter	Rating
Operating Temperature	-40°C to 85°C
Storage Temperature	-55°C to 125°C
Forward Current	10mA